

United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Aduces: COMMISSIONER FOR PATENTS P.O. Box 1430 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO	
10/042,673	01/08/2002	Xiaozhong Dang	RR-1765	RR-1765 6144	
24501 7	7590 07/01/2003				
MARK A LAUER 7041 KOLL CENTER PARKWAY SUITE 280			EXAMINER		
			NGUYEN, KHIEM D		
PLEASANTO	I, CA 94566		ART UNIT	PAPER NUMBER	
			2823	<u>~</u>	
			DATE MAILED: 07/01/2003		

Please find below and/or attached an Office communication concerning this application or proceeding.

`				
•		Application No.	Applicant(s)	<i>(</i> Q
Office Action Summary		10/042,673	DANG ET AL.	
		Examin r	Art Unit	
		Khiem D Nguyen	2823	
Period	The MAILING DATE of this communication app for Reply	pears on the cov r sh et with	the correspondence address	ş
TH - E a! - If - If	SHORTENED STATUTORY PERIOD FOR REPL E MAILING DATE OF THIS COMMUNICATION. Attensions of time may be available under the provisions of 37 CFR 1.1 fter SIX (6) MONTHS from the mailing date of this communication. The period for reply specified above is less than thirty (30) days, a rep NO period for reply is specified above, the maximum statutory period	136(a). In no event, however, may a repl ly within the statutory minimum of thirty (will apply and will expire SIX (6) MONTH	y be timely filed 30) days will be considered timely. S from the mailing date of this commun	ication.
- A	ailure to reply within the set or extended period for reply will, by statute ny reply received by the Office later than three months after the mailin arned patent term adjustment. See 37 CFR 1.704(b).			
Status	_			
1)[2				
2a)[2		his action is non-final.		
3)[Dispos	Since this application is in condition for allow closed in accordance with the practice under sition of Claims			ents is
· ·	☐ Claim(s) <u>1-20</u> is/are pending in the application	n		
7/2	4a) Of the above claim(s) is/are withdra			
5)[_			
	☐ Claim(s) 1-20 is/are rejected.			
7)[1
8)[or election requirement.		
Applic	ation Papers	•		
9)[The specification is objected to by the Examine	er.		
. 10)[The drawing(s) filed on 08 January 2002 is/are	e: a)⊠ accepted or b)☐ objecte	ed to by the Examiner.	
	Applicant may not request that any objection to the	ne drawing(s) be held in abeyand	ce. See 37 CFR 1.85(a).	
11)[The proposed drawing correction filed on	_ is: a)□ approved b)□ disa	approved by the Examiner.	
	If approved, corrected drawings are required in re	eply to this Office action.		
12)[The oath or declaration is objected to by the Ex	kaminer.		
Priorit	y under 35 U.S.C. §§ 119 and 120			
13)[Acknowledgment is made of a claim for foreig	n priority under 35 U.S.C. §	119(a)-(d) or (f).	
•	a)□ All b)□ Some * c)□ None of:			
	1. Certified copies of the priority document	ts have been received.		
	2. Certified copies of the priority document	ts have been received in App	olication No	
	3. Copies of the certified copies of the price application from the International But See the attached detailed Office action for a list	ureau (PCT Rule 17.2(a)).	-	е
	Acknowledgment is made of a claim for domest	•		lication\
· _	a) The translation of the foreign language pro	ovisional application has bee	n received.	ication).
	Acknowledgment is made of a claim for domes	tic priority under 35 U.S.C. §	3 120 and/or 121.	
Attachm		□	(DTO 110) T	
2) 🔲 No	otice of References Cited (PTO-892) otice of Draftsperson's Patent Drawing Review (PTO-948) formation Disclosure Statement(s) (PTO-1449) Paper No(s) _	5) Notice of Info	mmary (PTO-413) Paper No(s) ormal Patent Application (PTO-152	

Art Unit: 2823

DETAILED ACTION

Response to Arguments

Applicant's arguments with respect to claims 1-20 have been considered but are moot in view of the new ground(s) of rejection.

New Grounds of Rejection

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (e) the invention was described in-
- (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effect under this subsection of a national application published under section 122(b) only if the international application designating the United States was published under Article 21(2)(a) of such treaty in the English language; or
- (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that a patent shall not be deemed filed in the United States for the purposes of this subsection based on the filing of an international application filed under the treaty defined in section 351(a).
- 1. Claims 1-7 are rejected under 35 U.S.C. 102(e) as being anticipated by Hsu et al. (U.S. 2002/0191349).

Hsu disclose a method for forming an electromagnetic transducer, the method comprising (See paragraph [0057] to [0065] and FIG. 10A):

forming a first soft magnetic pole layer (FIG. 10A, 82/92) having a substantially flat surface;

forming an inorganic nonferromagnetic layer (FIG. 10A, 210) (alumina Al₂O₃) over the first pole layer;

Art Unit: 2823

forming a hardbaked photoresist mask (FIG. 10A, 208) over the inorganic nonferromagnetic layer wherein the mask terminating adjacent to a desired location of the second side;

chemically etching the hardbaked photoresist mask and the inorganic nonferromagnetic layer to create an inorganic nonferromagnetic apex region having a first side that is "substantially" parallel to the surface and a second side that is not parallel to the surface and not perpendicular to the surface (paragraph [0071] and FIG. 10A);

forming an inorganic dielectric layer (FIG. 10A, 205) adjacent to the inorganic nonferromagnetic apex region wherein forming an inorganic dielectric layer that partly covers the first soft magnetic pole layer, prior to forming the inorganic nonferromagnetic apex region;

forming an electrically conductive coil (FIG. 10A, 206) atop the inorganic dielectric layer;

forming a submicron inorganic nonferromagnetic layer (FIG. 10A, 214) adjacent to the region of inorganic nonferromagnetic material; and

forming a second soft magnetic pole layer (FIG. 10A, 232) over the inorganic nonferromagnetic apex region includes forming the second soft magnetic layer over the submicron inorganic nonferromagnetic layer, such that the second pole layer has an interface that is "substantially" equidistant from the second side.

2. Claims 8-14 are rejected under 35 U.S.C. 102(e) as being anticipated by Hsu et al. (U.S. 2002/0191349).

Art Unit: 2823

Hsu disclose a method for forming an electromagnetic transducer, the method comprising (See paragraph [0057] to [0065] and FIG. 10A):

forming a first soft magnetic pole layer (FIG. 10A, 82/92) having a substantially flat surface;

forming an inorganic nonferromagnetic layer (FIG. 10A, 210) (alumina Al₂O₃) over the first pole layer;

forming a photoresist mask atop the inorganic nonferromagnetic layer and curing the photoresist mask to form a hardbaked photoresist mask (FIG. 10A, 208);

etching the hardbaked photoresist mask and the inorganic nonferromagnetic layer, including removing the hardbaked photoresist mask, and thereby forming a region of inorganic nonferromagnetic region wherein forming region of inorganic nonferromagnetic material includes forming a side of the region that is not parallel and not perpendicular to the surface (paragraph [0071] and FIG. 10A);

forming an inorganic dielectric layer (FIG. 10A, 205) adjacent to region of inorganic nonferromagnetic material wherein forming an inorganic dielectric layer that partly covers the first soft magnetic pole layer, prior to forming the inorganic nonferromagnetic layer;

forming an electrically conductive coil (FIG. 10A, 206) atop the inorganic dielectric layer;

forming a submicron inorganic nonferromagnetic layer (FIG. 10A, 214) adjacent to the region of inorganic nonferromagnetic material; and

A STATE OF

Application/Control Number: 10/042,673

Art Unit: 2823

forming a second soft magnetic pole layer (FIG. 10A, 232) over the region of inorganic nonferromagnetic material and the submicron inorganic nonferromagnetic layer.

3. Claims 15-20 are rejected under 35 U.S.C. 102(e) as being anticipated by Hsu et al. (U.S. 2002/0191349).

Hsu disclose a method for forming an electromagnetic transducer, the method comprising (See paragraph [0057] to [0065] and FIG. 10A):

forming a first soft magnetic pole layer (FIG. 10A, 82/92) having a substantially flat surface;

forming an inorganic nonferromagnetic layer (FIG. 10A, 210) (alumina Al_2O_3) over the first pole layer;

forming a hardbaked photoresist mask (FIG. 10A, 208) over the inorganic nonferromagnetic layer wherein the mask terminating adjacent to a desired location of the sloping surface;

chemically etching the hardbaked photoresist mask and the inorganic nonferromagnetic layer to create an inorganic nonferromagnetic apex region over the first soft magnetic pole layer to have a sloping surface (paragraph [0071] and FIG. 10A);

forming an inorganic dielectric layer (FIG. 10A, 205) that partly covers the first soft magnetic pole layer, prior to forming the inorganic nonferromagnetic apex region;

forming an electrically conductive coil (FIG. 10A, 206) atop the inorganic dielectric layer;

Art Unit: 2823

forming a submicron inorganic nonferromagnetic layer (FIG. 10A, 214) adjacent to the inorganic nonferromagnetic apex region; and

forming a second soft magnetic pole layer (FIG. 10A, 232) over the inorganic nonferromagnetic apex region, such that the second pole layer has a region that is "substantially" parallel to the sloping surface and disposed within one micron of the sloping surface includes forming the second soft magnetic layer over the submicron inorganic nonferromagnetic layer.

Response to Amendment

Responding to applicant's Arguments

Applicant's arguments with respect to claims 1-20 have been considered but are moot in view of the new ground(s) of rejection.

Conclusion

Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the

Art Unit: 2823

advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Page 7

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Khiem D Nguyen whose telephone number is (703) 306-0210. The examiner can normally be reached on Monday-Friday (8:00 AM - 5:00 PM).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri can be reached on (703) 306-2794. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 746-9179 for regular communications and (703) 746-9179 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

K.N. June 24, 2003

> Olik Chaurhuri Supervisory Patent Examiner Technology Center 2800